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#### DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N5961 series devices are epoxy molded silicon NPN transistors, manufactured by the epitaxial planar process, designed for applications requiring extremely high gain (hFE) and low noise.

#### MARKING: FULL PART NUMBER

#### MAXIMUM RATINGS: (T<sub>A</sub>=25°C unless otherwise noted)

	SYMBOL	<u>2N5961</u>	<u>2N5962</u>	<u>2N5963</u>	UNITS
Collector-Base Voltage	V <sub>CBO</sub>	60	45	30	V
Collector-Emitter Voltage	V <sub>CEO</sub>	60	45	30	V
Emitter-Base Voltage	V <sub>EBO</sub>		7.0		V
Continuous Collector Current	ΙC		50		mA
Power Dissipation	PD		625		mW
Power Dissipation (T <sub>C</sub> =25°C)	PD		1.5		W
Operating and Storage Junction Temperature	TJ, Tsta		-65 to +150		°C

#### **ELECTRICAL CHARACTERISTICS:** (T<sub>A</sub>=25°C unless otherwise noted)

LLEOINIOA	CHARACTERISTICS: (TA-25 C u	2N5961			<u>2N5962</u>		2N5963	
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	MIN	MAX	UNITS
ICBO	V <sub>CB</sub> =Rated V <sub>CBO</sub>	-	2.0	-	2.0	-	2.0	nA
I <sub>CBO</sub>	V <sub>CB</sub> =Rated V <sub>CBO</sub> , T <sub>A</sub> =65°C	-	50	-	50	-	50	nA
IEBO	V <sub>EB</sub> =5.0V	-	1.0	-	1.0	-	1.0	nA
BVCBO	Ι <sub>C</sub> =10μΑ	60	-	45	-	30	-	V
BVCEO	I <sub>C</sub> =5.0mA	60	-	45	-	30	-	V
BVEBO	Ι <sub>Ε</sub> =10μΑ	7.0	-	7.0	-	7.0	-	V
V <sub>CE</sub> (SAT)	I <sub>C</sub> =10mA, I <sub>B</sub> =0.5mA, PW=300µs	-	0.2	-	0.2	-	0.2	V
V <sub>BE(ON)</sub>	V <sub>CE</sub> =5.0V, I <sub>C</sub> =1.0mA	0.5	0.7	0.5	0.7	0.5	0.7	V
hFE	$V_{CE}$ =5.0V, I <sub>C</sub> =10µA	100	-	450	-	900	-	
hFE	V <sub>CE</sub> =5.0V, I <sub>C</sub> =100µA	120	-	500	-	1.0K	-	
h <sub>FE</sub>	$V_{CE}$ =5.0V, I <sub>C</sub> =1.0mA	135	-	550	-	1.2K	-	
hFE	V <sub>CE</sub> =5.0V, I <sub>C</sub> =10mA	150	700	600	1.4K	1.2K	2.2K	
h <sub>fe</sub>	V <sub>CE</sub> =5.0V, I <sub>C</sub> =10mA, f=1.0kHz	150	1.0K	600	2.0K	1.2K	3.0K	
fΤ	V <sub>CE</sub> =5.0V, I <sub>C</sub> =10mA, f=100MHz	100	-	100	-	150	-	MHz
Cob	V <sub>CB</sub> =5.0V, I <sub>E</sub> =0	-	4.0	-	4.0	-	4.0	pF
C <sub>ib</sub>	V <sub>EB</sub> =0.5V, I <sub>C</sub> =0	-	6.0	-	6.0	-	6.0	pF

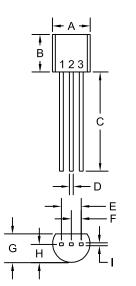
R1 (2-March 2016)



2N5961 2N5962 2N5963 SILICON NPN TRANSISTORS

ELECTRICAL CHARACTERISTICS - Continued: (T <sub>A</sub> =25°C unless otherwise noted)					
		<u>2N5961</u>	2N5962	<u>2N5963</u>	
SYMBOL	TEST CONDITIONS	MAX	MAX	MAX	UNITS
NF	$V_{CE}$ =5.0V, I <sub>C</sub> =100µA, R <sub>S</sub> =1.0kΩ, BW=400Hz, f=1.0kHz	6.0	6.0	6.0	dB
NF	$V_{CE}$ =5.0V, I <sub>C</sub> =100µA, R <sub>S</sub> =10kΩ, BW=400Hz, f=1.0kHz	-	4.0	3.0	dB
NF	$V_{CE}\text{=}5.0\text{V},~I_{C}\text{=}100\mu\text{A},~\text{R}_{S}\text{=}100\text{k}\Omega,~\text{BW}\text{=}400\text{Hz},~\text{f}\text{=}1.0\text{kHz}$	-	8.0	6.0	dB
NF	$V_{CE}$ =5.0V, I <sub>C</sub> =10µA, R <sub>S</sub> =10kΩ, BW=400Hz, f=1.0kHz	3.0	3.0	3.0	dB
NF	$V_{CE}$ =5.0V, I <sub>C</sub> =100µA, R <sub>S</sub> =1.0k $\Omega$ , BW=10Hz, f=10Hz	-	-	8.0	dB
NF*	$V_{CE}$ =5.0V, I <sub>C</sub> =10µA, R <sub>S</sub> =1.0kΩ, BW=15.7kHz,				
	f=10Hz to10kHz	3.0	3.0	3.0	dB

\* Wide Band Noise Figure



DIMENSIONS						
	INC	HES	MILLIMETERS			
SYMBOL	MIN	MAX	MIN	MAX		
A (DIA)	0.175	0.205	4.45	5.21		
В	0.170	0.210	4.32	5.33		
С	0.500	-	12.70	-		
D	0.016	0.022	0.41	0.56		
E	0.100		2.	2.54		
F	0.050		1.27			
G	0.125	0.165	3.18	4.19		
Н	0.080	0.105	2.03	2.67		
	0.015		0.38			
TO-92 (REV: R1)						

**LEAD CODE:** 1) Emitter

2) Base
3) Collector

R1

MARKING: FULL PART NUMBER

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R1 (2-March 2016)

## OUTSTANDING SUPPORT AND SUPERIOR SERVICES



## PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options

## DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2<sup>nd</sup> day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities

Special wafer diffusions

· Custom product packing

- PbSn plating options
- Package details
- Application notes
- Application and design sample kits

· Custom bar coding for shipments

Custom product and package development

### REQUESTING PRODUCT PLATING

- 1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

### CONTACT US

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